

#### 100V NPN MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 5.5A Continuous Collector Current
- I<sub>CM</sub> = 10A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 65mV @ 1A</li>
- $R_{SAT} = 43m\Omega$  @  $I_c = 6A$  for Low Equivalent On-Resistance
- h<sub>FE</sub> Specified up to 5.5A for High Gain Hold Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- · Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
   Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

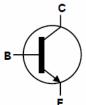
### **Applications**

- Line Switching
- Motor Driving (including DC fans)
- High-Side Switches
- Subscriber Line Interface Cards (SLIC)

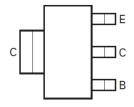




Top View



**Device Schematic** 



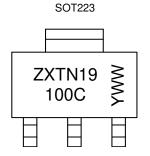
Pin-Out Top View

#### Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN19100CGTA	ZXTN19100C	7	12	1.000

- Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  - See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - 3. Hallogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



ZXTN19 100C = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



# **Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	5.5	Α
Peak Pulse Current	I <sub>CM</sub>	10	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	D	3.0 24	W mW/°C
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.6 12.8	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{ heta JA}$	42	
mermai nesistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	78	°C/W
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	8.8	1
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## ESD Ratings (Note 8)

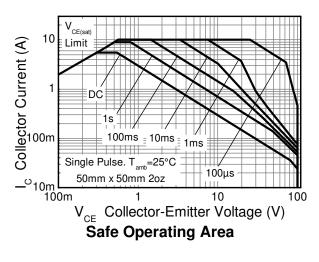
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

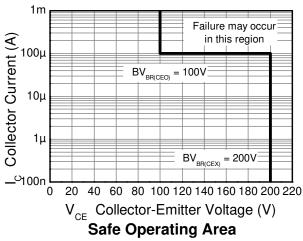
Notes:

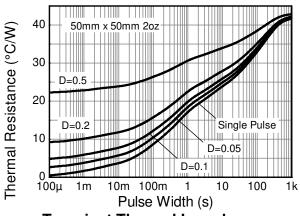
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz. copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
  6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

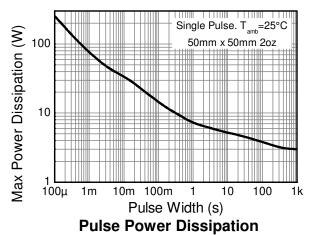


### **Thermal Characteristics and Derating Information**

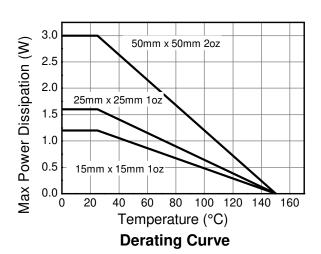








**Transient Thermal Impedance** 





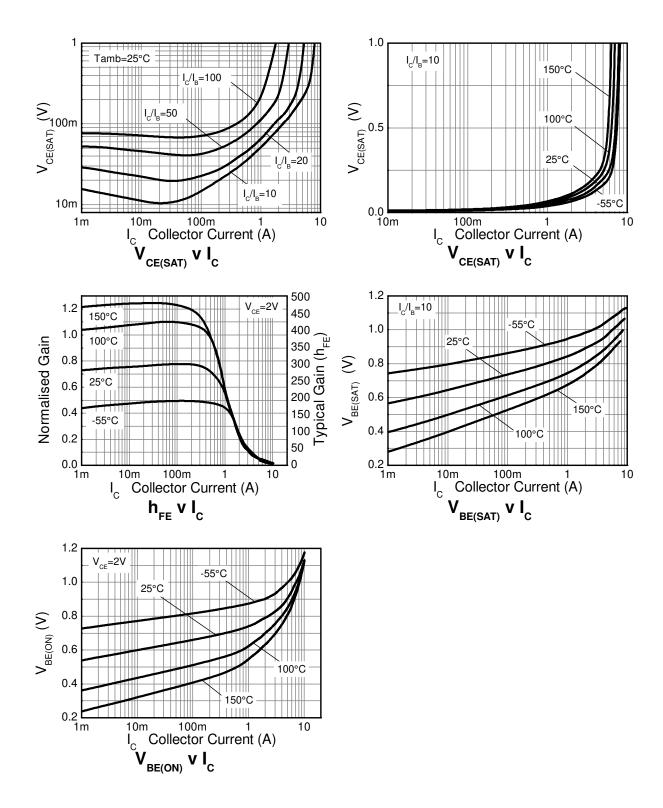
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		200	240	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)		100	120	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>ECO</sub>	5	8	-	V	$I_E = 100\mu A$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3		V	$I_E = 100\mu A$
Collector Cutoff Current	I <sub>CBO</sub>	_	<1 —	50 0.5	nA μA	V <sub>CB</sub> = 200V V <sub>CB</sub> = 200V, T <sub>A</sub> = +100°C
Collector Cutoff Current	I <sub>CEX</sub>	_	_	100	nA	$V_{CB} = 200V, R_{BE} < 1k\Omega$
Emitter Cutoff Current	I <sub>EBO</sub>	_	<1	50	nA	V <sub>EB</sub> = 5.6V
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	_	50 110 245	65 140 430	mV	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA I <sub>C</sub> = 1A, I <sub>B</sub> = 20mA I <sub>C</sub> = 5.5A, I <sub>B</sub> = 550mA
Base-Emitter Saturation Voltage (Note 9)		_	1.005	1.1	V	I <sub>C</sub> = 5.5A, I <sub>B</sub> = 550mA
Base-Emitter Turn-on Voltage (Note 9)		_	0.95	1.05	V	I <sub>C</sub> = 5.5A, V <sub>CE</sub> = 2V
DC Current Gain (Note 9)	V <sub>BE(on)</sub>	200 130	300 190 25	500		$I_C = 100$ mA, $V_{CE} = 2V$ $I_C = 1$ A, $V_{CE} = 2V$ $I_C = 5.5$ A, $V_{CE} = 2V$
Transition Frequency		_	150	1	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA, f = 50MHz
Input Capacitance		_	305	400	pF	V <sub>EB</sub> = 0.5V, f = 1MHz
Output Capacitance (Note 9)		_	15.7	25	pF	V <sub>CB</sub> = 10V, f = 1MHz
On the later of Theory	ton	_	51.9	-		$V_{CC} = 10V, I_{C} = 500mA,$
Switching Times	toff		1,095	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



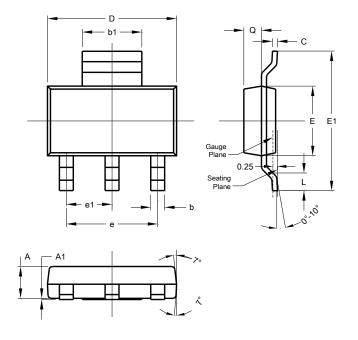
# $\textbf{Typical Electrical Characteristics} \ (@T_{A} = +25^{\circ}C, \ unless \ otherwise \ specified.)$





# **Package Outline Dimensions**

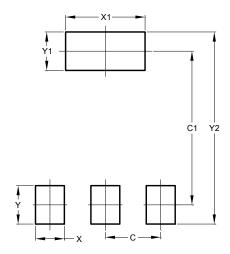
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
C2	8.00		



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